

VERSION SHOWING THE CHANGES TO THE CLAIMS

This listing replaces all prior listings of the claims.

IN THE CLAIMS:

Amend the claims as follows:

1 (Currently amended) An organic electronic component with ~~comprising~~ a patterned upper functional layer having a thickness of at most about less than 100 nm deposited on one of a lower layer and a substrate layer, the patterning arising by virtue of a lower functional layer being only partially wetted with the organic functional material of the next functional layer

the component being formed by patterning the upper functional layer by treatment of the one layer in which a first partial region of the one layer is wetted by the upper functional layer when applied to the one layer and a second partial region of the one layer is not wetted by the deposited upper layer and therefore is free of the functional layer to thereby pattern the upper functional layer on the lower layer.

2 (Original) The organic electronic component as claimed in claim 1, in which the patterned functional layer is a semiconducting functional layer.

Claim 3, canceled.

4 (Currently amended). The method as claimed in claim 10 ~~3~~, in which the applied upper layer comprises a patterned semiconducting functional layer is produced in patterned fashion.

Claim 5, canceled

Add the following claims:

6 (New). An organic electronic component comprising:

a substrate;

one of a lower functional layer and a lower substrate layer having a predetermined area; and

a patterned functional upper layer on the one lower layer having a thickness at most of about 100 nm, the one lower layer including an arrangement to prevent wetting by the upper layer in the predetermined area as the patterned functional upper layer is applied to the one lower layer including the predetermined area so that the upper layer only partially wets the lower layer to form a lower layer region free of the upper layer in the predetermined area.

7 (New). An organic electronic component comprising:

one of a lower functional layer and a lower substrate layer having a given area; and

a patterned functional upper layer on the one lower layer having a thickness at most of about 100 nm, the one lower layer being formed by an arrangement to prevent wetting by the upper layer of at least a portion of the given area so that the upper layer only partially wets the lower layer to form the pattern.

8. (New) An organic component according to claim 1 wherein the one lower layer includes an arrangement to prevent the wetting by the upper layer.

9 (New) An organic component according to claim 7 wherein the one lower layer includes an arrangement to prevent the wetting by the upper layer.

10 (New). A method for producing an organic electronic component comprising:

forming one of a lower functional layer and a lower substrate layer ;

applying an upper functional layer to the one lower layer; and

preventing the applied upper functional layer from wetting the one lower layer in at least a portion of the one lower layer to form the applied upper layer into a pattern on the one lower layer .

11 (New). The method of claim 10 wherein the preventing step includes printing a resist layer on the portion of the lower layer.

12 (New). The method of claim 10 wherein the preventing step includes printing a treatment on the portion of the lower layer.

13 (New). A circuit formed of organic functional layers comprising:

a substrate; and

a plurality of adjacent organic electronic components on the substrate, each component comprising one or more conductive functional layer electrodes and a patterned semiconducting layer on the one or more electrodes;

the patterned semiconducting functional layer having a thickness no greater than about 100 nm, the patterned semiconducting functional layer having an electrical interruption between next adjacent components.

14 (New). The circuit of claim 13 wherein the electrical interruption comprises a semiconducting free area on the substrate.

15 (New). The circuit of claim 13 wherein at least one of the components is a transistor.

16 (New). The circuit of claim 14 wherein the free area is formed by preventing the semiconducting functional layer applied over that free area from wetting the substrate in that free area.

17 (New). The circuit of claim 16 including an arrangement on the substrate in the free area for said preventing.

18 (New). The circuit of claim 17 wherein the arrangement includes a resist on the substrate.

19 (New). The circuit of claim 17 wherein the arrangement includes a surface treatment applied to the substrate in the free area for said preventing.